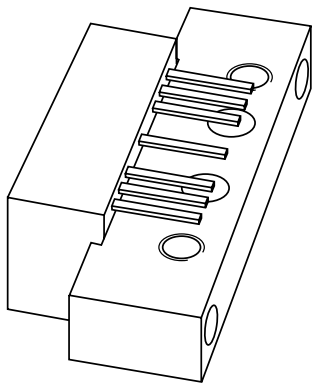


DATA SHEET



BGD802

860 MHz, 18.5 dB gain power
doubler amplifier

Product specification
Supersedes data of 2001 Oct 30

2002 Jan 23



860 MHz, 18.5 dB gain power doubler amplifier

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FEATURES

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

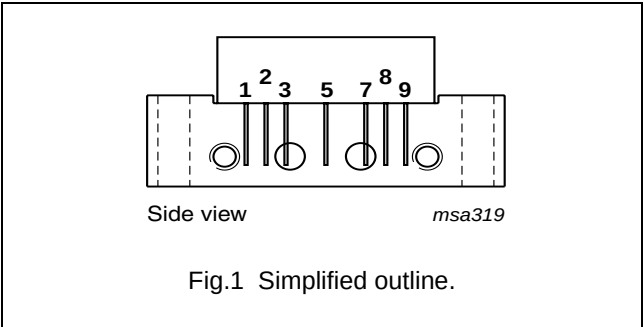
- CATV systems operating in the 40 to 860 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating at a supply voltage of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2, 3	common
5	+V _B
7, 8	common
9	output



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	18	19	dB
		f = 860 MHz	18.5	–	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	–	410	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _B	supply voltage	–	25	V
V _i	RF input voltage	–	65	dBmV
T _{stg}	storage temperature	–40	+100	°C
T _{mb}	operating mounting base temperature	–20	+100	°C

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CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; $V_B = 24$ V; $T_{case} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	18.5	19	dB
		$f = 860$ MHz	18.5	19.5	–	dB
SL	slope cable equivalent	$f = 40$ to 860 MHz	0.2	1.1	2	dB
FL	flatness of frequency response	$f = 40$ to 860 MHz	–	± 0.2	± 0.5	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	35	–	dB
		$f = 80$ to 160 MHz	18.5	31	–	dB
		$f = 160$ to 320 MHz	17	27	–	dB
		$f = 320$ to 640 MHz	15.5	22	–	dB
		$f = 640$ to 860 MHz	14	20	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	29.5	–	dB
		$f = 80$ to 160 MHz	18.5	29	–	dB
		$f = 160$ to 320 MHz	17	25.5	–	dB
		$f = 320$ to 640 MHz	15.5	23	–	dB
		$f = 640$ to 860 MHz	14	22	–	dB
S_{21}	phase response	$f = 50$ MHz	–45	–	+45	deg
CTB	composite triple beat	49 channels flat; $V_o = 47$ dBmV; measured at 859.25 MHz	–	–66	–63	dB
X_{mod}	cross modulation	49 channels flat; $V_o = 47$ dBmV; measured at 55.25 MHz	–	–65	–62	dB
CSO	composite second order distortion	49 channels flat; $V_o = 47$ dBmV; measured at 860.5 MHz	–	–67.5	–60	dB
d_2	second order distortion	note 1	–	–75	–69	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	61.5	63.5	–	dBmV
NF	noise figure	$f = 50$ MHz	–	4.5	5.5	dB
		$f = 550$ MHz	–	–	6	dB
		$f = 650$ MHz	–	–	7	dB
		$f = 750$ MHz	–	–	7.5	dB
		$f = 860$ MHz	–	6.5	9	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 805.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 860.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 851.25$ MHz; $V_p = V_o$;
 $f_q = 858.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 860.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 849.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

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Table 2 Bandwidth 40 to 860 MHz; $V_B = 24\text{ V}$; $T_{\text{case}} = 30\text{ }^{\circ}\text{C}$; $Z_S = Z_L = 75\text{ }\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 50\text{ MHz}$	18	18.5	19	dB
		$f = 860\text{ MHz}$	18.5	19.5	–	dB
SL	slope cable equivalent	$f = 40\text{ to }860\text{ MHz}$	0.2	1.1	2	dB
FL	flatness of frequency response	$f = 40\text{ to }860\text{ MHz}$	–	± 0.2	± 0.5	dB
S_{11}	input return losses	$f = 40\text{ to }80\text{ MHz}$	20	35	–	dB
		$f = 80\text{ to }160\text{ MHz}$	18.5	31	–	dB
		$f = 160\text{ to }320\text{ MHz}$	17	27	–	dB
		$f = 320\text{ to }640\text{ MHz}$	15.5	22	–	dB
		$f = 640\text{ to }860\text{ MHz}$	14	20	–	dB
S_{22}	output return losses	$f = 40\text{ to }80\text{ MHz}$	20	29.5	–	dB
		$f = 80\text{ to }160\text{ MHz}$	18.5	29	–	dB
		$f = 160\text{ to }320\text{ MHz}$	17	25.5	–	dB
		$f = 320\text{ to }640\text{ MHz}$	15.5	23	–	dB
		$f = 640\text{ to }860\text{ MHz}$	14	22	–	dB
S_{21}	phase response	$f = 50\text{ MHz}$	–45	–	+45	deg
CTB	composite triple beat	129 channels flat; $V_o = 44\text{ dBmV}$; measured at 859.25 MHz	–	–56.5	–54	dB
X_{mod}	cross modulation	129 channels flat; $V_o = 44\text{ dBmV}$; measured at 55.25 MHz	–	–61	–59	dB
CSO	composite second order distortion	129 channels flat; $V_o = 44\text{ dBmV}$; measured at 860.5 MHz	–	–64.5	–56	dB
d_2	second order distortion	note 1	–	–75	–69	dB
V_o	output voltage	$d_{\text{im}} = -60\text{ dB}$; note 2	61.5	63	–	dBmV
NF	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

- $f_p = 55.25\text{ MHz}$; $V_p = 44\text{ dBmV}$;
 $f_q = 805.25\text{ MHz}$; $V_q = 44\text{ dBmV}$;
measured at $f_p + f_q = 860.5\text{ MHz}$.
- Measured according to DIN45004B:
 $f_p = 851.25\text{ MHz}$; $V_p = V_o$;
 $f_q = 858.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_r = 860.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
measured at $f_p + f_q - f_r = 849.25\text{ MHz}$.
- The module normally operates at $V_B = 24\text{ V}$, but is able to withstand supply transients up to 30 V.

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Table 3 Bandwidth 40 to 750 MHz; $V_B = 24$ V; $T_{case} = 30$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	18.5	19	dB
		$f = 750$ MHz	18.5	19.4	–	dB
SL	slope cable equivalent	$f = 40$ to 750 MHz	0.2	–	2	dB
FL	flatness of frequency response	$f = 40$ to 750 MHz	–	–	± 0.5	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	35	–	dB
		$f = 80$ to 160 MHz	18.5	31	–	dB
		$f = 160$ to 320 MHz	17	27	–	dB
		$f = 320$ to 640 MHz	15.5	22	–	dB
		$f = 640$ to 750 MHz	14	20	–	dB
S_{22}	output return losses	$f = 40$ to 80 MHz	20	29.5	–	dB
		$f = 80$ to 160 MHz	18.5	29	–	dB
		$f = 160$ to 320 MHz	17	25.5	–	dB
		$f = 320$ to 640 MHz	15.5	23	–	dB
		$f = 640$ to 750 MHz	14	22	–	dB
S_{21}	phase response	$f = 50$ MHz	–45	–	+45	deg
CTB	composite triple beat	110 channels flat; $V_o = 44$ dBmV; measured at 745.25 MHz	–	–60.5	–58	dB
X_{mod}	cross modulation	110 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz	–	–62.5	–60	dB
CSO	composite second order distortion	110 channels flat; $V_o = 44$ dBmV; measured at 746.5 MHz	–	–66	–60	dB
d_2	second order distortion	note 1	–	–	–72	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	64	–	–	dBmV
NF	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 691.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 746.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 740.25$ MHz; $V_p = V_o$;
 $f_q = 747.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 749.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 738.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

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Table 4 Bandwidth 40 to 550 MHz; $V_B = 24$ V; $T_{case} = 30$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	18	18.5	19	dB
		$f = 550$ MHz	18.5	19.3	–	dB
SL	slope cable equivalent	$f = 40$ to 550 MHz	0.2	–	2	dB
FL	flatness of frequency response	$f = 40$ to 550 MHz	–	–	± 0.3	dB
S_{11}	input return losses	$f = 40$ to 80 MHz	20	35	–	dB
		$f = 80$ to 160 MHz	18.5	31	–	dB
		$f = 160$ to 320 MHz	17	27	–	dB
		$f = 320$ to 550 MHz	16	22	–	dB
S_{22}	input return losses	$f = 40$ to 80 MHz	20	29.5	–	dB
		$f = 80$ to 160 MHz	18.5	29	–	dB
		$f = 160$ to 320 MHz	17	25.5	–	dB
		$f = 320$ to 550 MHz	16	23	–	dB
S_{21}	phase response	$f = 50$ MHz	–45	–	+45	deg
CTB	composite triple beat	77 channels flat; $V_o = 44$ dBmV; measured at 547.25 MHz	–	–67	–65	dB
X_{mod}	cross modulation	77 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz	–	–66	–63	dB
CSO	composite second order distortion	77 channels flat; $V_o = 44$ dBmV; measured at 548.5 MHz	–	–67	–63	dB
d_2	second order distortion	note 1	–	–	–72	dB
V_o	output voltage	$d_{im} = -60$ dB; note 2	65	–	–	dBmV
NF	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 493.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 548.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 540.25$ MHz; $V_p = V_o$;
 $f_q = 547.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 549.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 538.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

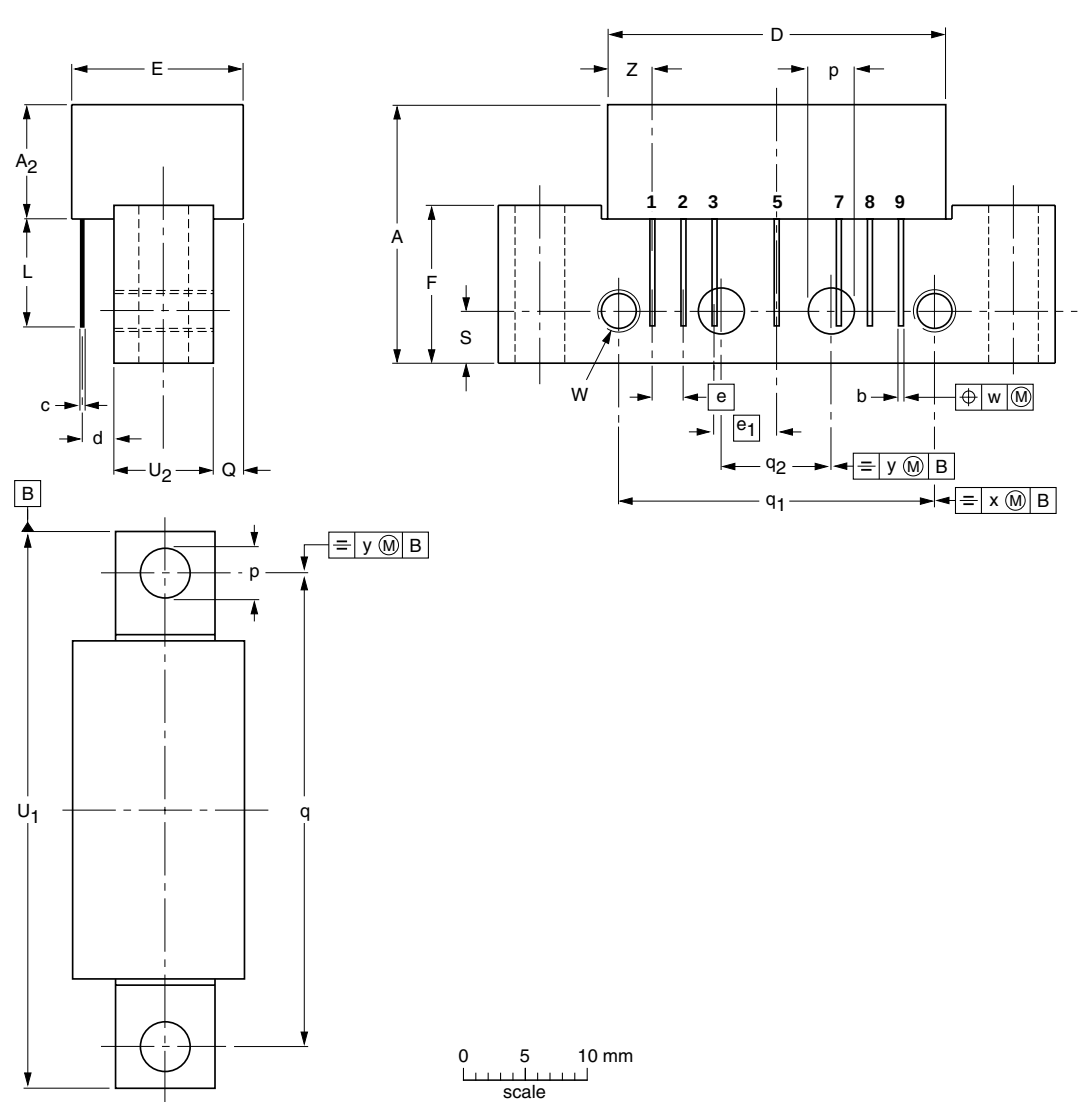
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;
2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₂ max.	b	c	D max.	d	E max.	e	e ₁	F	L min.	p	Q max.	q	q ₁	q ₂	S	U ₁	U ₂	W	w	x	y	Z max.
mm	20.8	9.5	0.51 0.38	0.25	27.2	2.04 2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75 44.25	8.2 7.8	6-32 UNC	0.25	0.7	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT115J						04-02-04 10-06-18

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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